

Isc N-Channel MOSFET Transistor

STP60NF06FP

• FEATURES

- Typical $R_{DS(on)}=0.08 \Omega$
- With low gate drive requirements
- Easy to drive
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

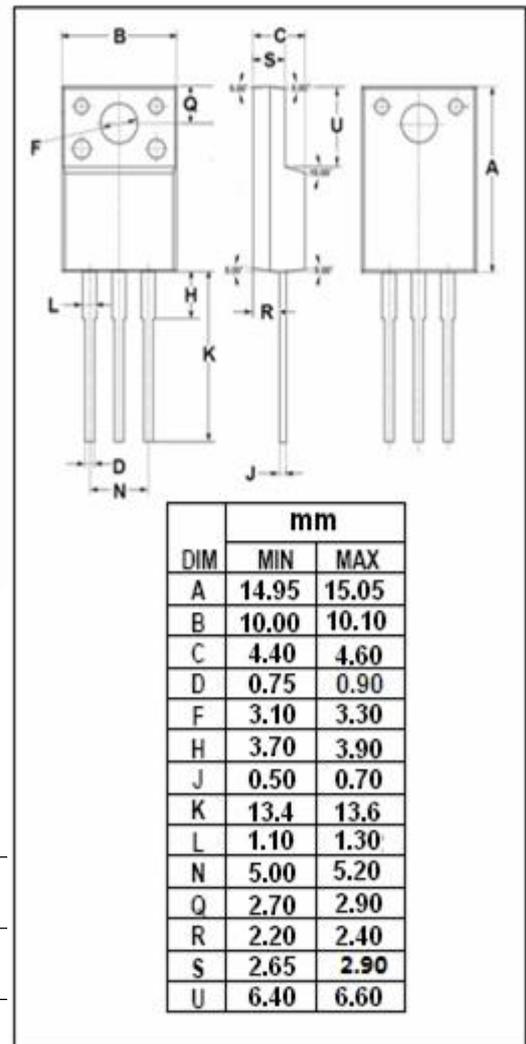
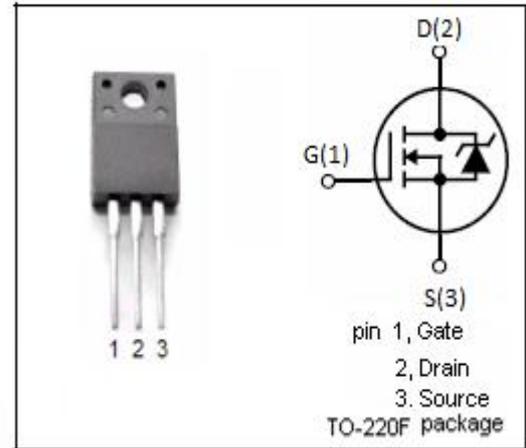
- Solenoid and relay drivers
- DC-DC converters
- Automotive environment

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous@ $T_c=25^\circ C$ $T_c=100^\circ C$	11 7.5	A
I_{DM}	Drain Current-Single Pulsed	44	A
P_D	Total Dissipation	25	W
T_j	Operating Junction Temperature	-55~175	$^\circ C$
T_{stg}	Storage Temperature	-55~175	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	6	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62.5	$^\circ C/W$



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ELECTRICAL CHARACTERISTICS

 T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	60			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =±20V; I _D =0.25mA	24			V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =8A		80	100	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 60V; V _{GS} = 0V; T _J =25°C T _J =125°C			1 10	μA
V _{SDF}	Diode forward voltage	I _{SD} =16A, V _{GS} = 0 V			1.3	V